# **ON Semiconductor**



Final Product/Process Change Notification Document # : FPCN20984X

Issue Date: 22 July 2015

| Title of Change:   | Foundry capacity expansion to Hangzhou Silan Integrated Circuit Co. LTD (Silan) and op amp & comparator design change for all wafer fab facilities   |  |  |
|--|--|--|--|
| Proposed first ship date:  | 29 October 2015  |  |  |
| Contact information:   | Contact your local ON Semiconductor Sales Office or <shannon.riggs@onsemi.com></shannon.riggs@onsemi.com>  |  |  |
| Samples:   | Contact your local ON Semiconductor Sales Office   |  |  |
| Additional Reliability Data:   | Contact your local ON Semiconductor Sales Office or <ken.fergus@onsemi.com>.</ken.fergus@onsemi.com>   |  |  |
| Type of notification:  | This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change.<br>ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact <pcn.support@onsemi.com>.</pcn.support@onsemi.com> |  |  |
| Change Part Identification:  | Changed part identification will be distinguished by manufacturing date code and lot traceability. Changed material will be sourced on or after W40, 2015 depending on inventory depletion schedules.<br>External package labels (bar codes) will identify the fab source location.  |  |  |
| Change category:   | Wafer Fab Change Assembly Change Test Change Other   |  |  |
| Change Sub-Category(s):<br>Manufacturing Site Change/<br>Manufacturing Process Char<br>Sites Affected:   | Addition Material Change Datasheet/Product Doc change   Addition Material Change Shipping/Packaging/Marking   nge Product specific change Other: _Design Change  |  |  |
| ☐ All site(s) 	☐ not ap  | plicable ON Semiconductor site(s) : I External Foundry/Subcon site(s)<br>ON Roznov, Czech Republic Hangzhou Silan Integrated Circuit<br>Co., LTD   |  |  |
| Description and Purpose:<br>In order to provide best in class supply continuity, ON Semiconductor is pleased to announce Hangzhou Silan Integrated Circuit Co. LTD (Silan) |  |  |  |

has been qualified as an alternate supply source for general purpose, bipolar analog op-amp and comparator products. Additionally, and as part of ON Semiconductor's continuous improvement efforts, the affected designs have been modified in both the ON Semiconductor's Rosnov (Rosnov) and Silan wafer fabrication facilities. Both fab locations will provide the same design version of products, and parts will be pin-for-pin replacements for existing devices, with no change in part nomenclature.



#### **Reliability Data Summary:**

## Roznov Wafer Fab QV DEVICE NAME: One lot LM393, two lots LM358 PACKAGE: Soic 8/14

| Test | Specification       | Condition                     | Interval | Results |
|------|---------------------|-------------------------------|----------|---------|
| HTOL | JESD22-A108         | Ta=125°C, 100 % max rated Vcc | 1008 hrs | 0/240   |
| тс   | JESD22-A104         | Ta= -65°C to +150°C           | 500 сус  | 0/240   |
| HAST | JESD22-A110         | 130°C, 85% RH, 18.8psig, bias | 96 hrs   | 0/240   |
| PC   | J-STD-020 JESD-A113 | MSL 1 @ 260 °C                |          |         |

## Silan Wafer Fab QV DEVICE NAME: One lot LM393, two lots LM358 PACKAGE: Soic 8/14

| Test  | Specification       | Condition                         | Interval | Results |
|-------|---------------------|-----------------------------------|----------|---------|
| HTOL  | JESD22-A108         | Ta=125°C, 100 % max rated Vcc     | 1008 hrs | 0/240   |
| ELFR  | JESD22-A108         | Ta=125C, 100% max rated Vcc       | 48 hrs   | 0/2400  |
| HTSL  | JESD22-A103         | Ta= 150°C                         | 1008 hrs | 0/240   |
| тс    | JESD22-A104         | Ta= -65°C to +150°C               | 500 сус  | 0/240   |
| HAST  | JESD22-A110         | 130°C, 85% RH, 18.8psig, bias     | 96 hrs   | 0/240   |
| uHAST | JESD22-A118         | 130°C, 85% RH, 18.8psig, unbiased | 96 hrs   | 0/240   |
| PC    | J-STD-020 JESD-A113 | MSL 1 @ 260 °C                    |          |         |

## **Electrical Characteristic Summary:**

Electrical characterization has been completed with no changes to the AC/DC specifications. ON Semiconductor recommends samples be obtained for application specific review and validation.

As a result of the design modification, the ESD capability will be revised as follows:

| Device     | from | HBM (V) | MM (V) | to | HBM (V) | MM (V) |
|------------|------|---------|--------|----|---------|--------|
| LM358DR2G  | from | 2000    | 200    | to | 250     | 100    |
| LM324DR2G  | from | 2000    | 200    | to | 200     | 100    |
| LM393DR2G  | from | 1500    | 150    | to | 250     | 100    |
| LM339DR2G  | from | 1500    | 200    | to | 250     | 100    |
| LM2901DR2G | from | 1500    | 200    | to | 250     | 100    |
| LM2902DR2G | from | 2000    | 200    | to | 200     | 100    |
| LM2903DR2G | from | 1500    | 150    | to | 250     | 100    |
| LM2904DR2G | from | 2000    | 200    | to | 250     | 100    |
|            |      |         |        |    |         |        |



| List of affected Standard Parts: |                       |  |  |
|----------------------------------|-----------------------|--|--|
| Part Number                      | Qualification Vehicle |  |  |
| LM358DR2G                        | LM393DR2G + LM324DR2G |  |  |
| LM324DR2G                        | LM393DR2G + LM324DR2G |  |  |
| LM393DR2G                        | LM393DR2G + LM324DR2G |  |  |
| LM339DR2G                        | LM393DR2G + LM324DR2G |  |  |
| LM2901DR2G                       | LM393DR2G + LM324DR2G |  |  |
| LM2902DR2G                       | LM393DR2G + LM324DR2G |  |  |
| LM2903DR2G                       | LM393DR2G + LM324DR2G |  |  |
| LM2904DR2G                       | LM393DR2G + LM324DR2G |  |  |